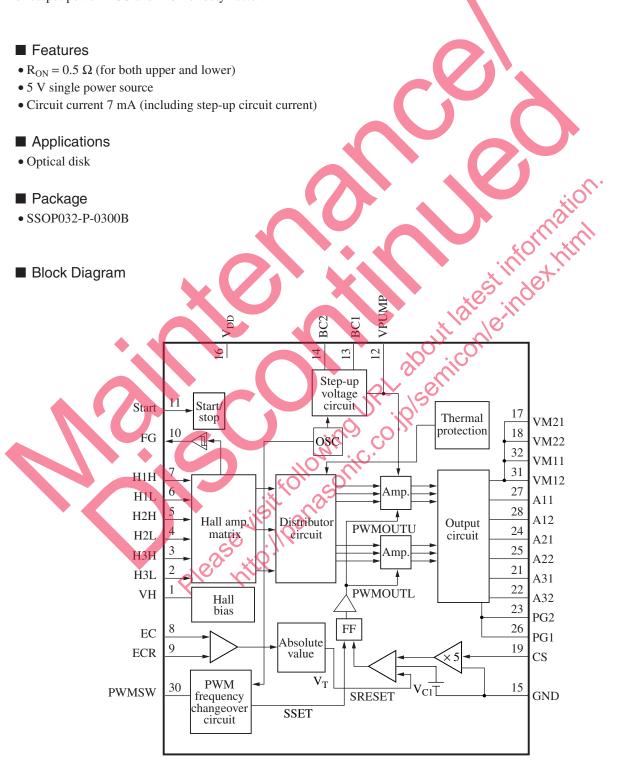
# **AN8473SA**

# Spindle motor driver IC for optical disk

#### Overview

The AN8473SA is an optical disk driver IC, featuring direct PWM drive, DMOS power drive, low ON resistance of output power MOS and 120° of duty-factor.



#### ■ Pin Descriptions

Pin No.	Symbol	Description	Pin No.	Symbol	Description
1	VH	Hall bias pin	17	VM21	Motor supply voltage pin 2
2	H3L	Hall element-3 negative input pin	18	VM22	Motor supply voltage pin 2
3	НЗН	Hall element-3 positive input pin	19	CS	Current det. pin
4	H2L	Hall element-2 negative input pin	20	N.C.	N.C.
5	Н2Н	Hall element-2 positive input pin	21	A31	Drive output 3
6	H1L	Hall element-1 negative input pin	22	A32	Drive output 3
7	H1H	Hall element-1 positive input pin	23	PG2	Power current det. pin 2
8	EC	Torque command input pin	24	A21	Drive output 2
9	ECR	Torque command reference input pin	25	A22	Drive output 2
10	FG	FG signal output pin	26	PG1	Power current det. pin 1
11	Start	Start/stop changeover pin	27	A11	Drive output 1
12	VPUMP	Booster pin	28	A12	Drive output 1
13	BC1	Booster capacitor connection pin 1	29	N.C.	N.C.
14	BC2	Booster capacitor connection pin 2	30	PWMSW	PWM frequency changeover pin
15	GND	Ground pin	31	VM12	Motor supply voltage pin 1
16	$V_{\mathrm{DD}}$	Supply voltage pin	32	VM11	Motor supply voltage pin 1

## ■ Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Supply voltage *2	$V_{DD}$	IRL ISEMICE	V
	V <sub>M11, 12</sub>		
	V <sub>M21, 22</sub>	U iols	
Drive output voltage *5	$V_{(m)}$		V
Control signal input voltage *6	$V_{(n)}$	O to V <sub>DD</sub>	V
Supply current	I <sub>DD</sub>	30	mA
Drive output current *4	$I_{(o)}$	±1 200	mA
Hall bias current *7	$I_{HB(n)}$	30	mA
Power dissipation *3	PD	293	mW
Operating ambient temperature *100	Topr	-30  to  +85	°C
Storage temperature *1	$T_{stg}$	-55 to +150	°C

Note) Do not apply external currents or voltages to any pins not specifically mentioned.

For circuit currents, '+' denotes current flowing into the IC, and '-' denotes current flowing out of the IC.

- \*1: Except for the operating ambient temperature and storage temperature, all ratings are for  $T_a = 25$ °C.
- \*2: The voltage in the step-up voltage circuit exceeds the supply voltage.

  For the allowable value of the step-up voltage, refer to "■ Electrical Characteristics".
- \*3: The power dissipation shown is the value of independent IC without a heat sink at  $T_a = 70^{\circ}$ C. Refer to the  $P_D T_a$  curves of the "Application Notes" for details.
- \*4: o = 17, 18, 21, 22, 23, 24, 25, 26, 27, 28, 31, 32
- \*5: m = 21, 22, 24, 25, 27, 28

\*6: n = 2, 3, 4, 5, 6, 7, 8, 9, 11, 30

\*7: n = 1

# ■ Recommended Operating Range

Parameter	Symbol	Range	Unit
Supply voltage	$V_{DD}$	4.5 to 5.5	V
	V <sub>M11, 12</sub>		
	V <sub>M21, 22</sub>		

# ■ Electrical Characteristics at $T_a = 25$ °C

$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Circuit current 2         I <sub>DD2</sub> V <sub>DD</sub> = 5 V including step-up circuit         — 7 14 mA         MA           Start/stop         Start voltage         V <sub>START</sub> at $V_{DD} = 5$ V and $1 \rightarrow H$ 2.7 — — V         V           Stop voltage         V <sub>STOP</sub> voltage with which a circuit operates at $V_{DD} = 5$ V and $1 \rightarrow H$ 2.7 — — V         V           Hall bias         V <sub>STOP</sub> voltage with which a circuit becomes aff at $V_{DD} = 5$ V and $1 \rightarrow H$ 0.7 V.2 V.6 V         V           Hall bias voltage         V <sub>HB</sub> V <sub>DD</sub> = 5 V, I <sub>HB</sub> = 20 mA         0.7 V.2 V.6 V         V           Hall amplifier         Input bias current         I <sub>BH</sub> V <sub>DD</sub> = 5 V         1 5 μA           In-phase input voltage range         V <sub>HBR</sub> V <sub>DD</sub> = 5 V, except for H2H, H2L V         — 4.0 V           Minimum input level         V <sub>NH</sub> V <sub>ND</sub> = 5 V         60 — mVIp-pl           Torque command         In-phase input voltage range         EC V <sub>DD</sub> = 5 V         0.5 — 3.9 V           Offset voltage         EC O <sub>F</sub> V <sub>DD</sub> = 5 V         0 75 150 mV           Dead zone         EC D <sub>D</sub> V <sub>DD</sub> = 5 V         0 75 150 mV           Input outrent         EC D <sub>D</sub> V <sub>DD</sub> = 5 V, I <sub>C</sub> = 500 mA         — 0.15 0.30 V           Low-level output saturation voltage         V <sub>DD</sub> = 5 V, I <sub>C</sub> = 500 mA         — 0.15 0.30 V           Low-level output saturation voltage	Overall						
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Circuit current 1	$I_{\mathrm{DD1}}$	$V_{DD} = 5 \text{ V}$ in power save mode		0	0.2	mA
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Circuit current 2	$I_{\mathrm{DD2}}$	$V_{\rm DD} = 5 \text{ V}$ including step-up circuit	_	7	14	mA
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Start/stop					P	
Hall bias  Hall bias voltage  VHB  VDD = 5 V, IHB = 20 mA  0.7 V.2 V6  V  Hall amplifier  Input bias current  Input bias current  Input bias current  VHBR  VDD = 5 V, except for H2H, H21  VDD = 5 V  Minimum input level  VINH  VDD = 5 V  Offset voltage fange  EC VDD = 5 V  Offset voltage  EC DD = 5 V  DD = 5 V  Offset voltage  EC DD = 5 V  DD =	Start voltage	V <sub>START</sub>	V 2	2.7		_	V
Hall bias voltage	Stop voltage	V <sub>STOP</sub>			_	0.70	V
Hall amplifier   Input bias current   I <sub>BH</sub>   V <sub>DD</sub> = 5 V   C   1   5   μA   In-phase input voltage range   V <sub>IBR</sub>   V <sub>DD</sub> = 5 V, except for H2H, H2D   C   C   C   C   C   C   C   C   C	Hall bias				'M'	, , (	
Input bias current   I_{BH}	Hall bias voltage	$V_{\mathrm{HB}}$	$V_{DD} = 5 \text{ V}, I_{HB} = 20 \text{ mA}$	0.7	1.2	1.6	V
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Hall amplifier			S	Se	7	
	Input bias current	$I_{BH}$	$V_{DD} = 5 V$		(1	5	μΑ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	In-phase input voltage range	$V_{HBR}$	$V_{DD} = 5 \text{ V}$ , except for H2H, H2L	1.5		4.0	V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Minimum input level	V <sub>INH</sub>	$V_{DD} = 5 \text{ V}$	60		_	mV[p-p]
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Torque command		ol a Mi				
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	In-phase input voltage range	EC	$V_{DD} = 5 \text{ V}$	0.5		3.9	V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Offset voltage	EC <sub>OF</sub>	$V_{DD} = 5 \text{ V}$	-100	0	100	mV
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Dead zone	EC <sub>DZ</sub>	$V_{DD} = 5 \text{ W}$	0	75	150	mV
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Input current	ECIN	$V_{DD} = 5 \text{ V}, EC = ECR = 2.5 \text{ V}$	-5	-1	_	μΑ
High-level output saturation voltage $V_{OH}$ $V_{DD} = 5 \text{ V}$ , $I_O = -500 \text{ mA}$ —0.150.30VLow-level output saturation voltage $V_{OL}$ $V_{DD} = 5 \text{ V}$ , $I_O = 500 \text{ mA}$ —0.150.30VTorque limit current $I_{TL}$ $V_{DD} = 5 \text{ V}$ , $R_{CS} = 0.33 \Omega$ 455570685mAFGFG output high-level $FG_H$ $V_{DD} = 5 \text{ V}$ , $I_{FG} = -0.01 \text{ mA}$ 3——VFG output low-level $FG_L$ $V_{DD} = 5 \text{ V}$ , $I_{FG} = 0.01 \text{ mA}$ ——0.5VIn-phase input voltage range $V_{FGR}$ $V_{DD} = 5 \text{ V}$ 1.5—3.0VFG hysteresis width $H_{FG}$ $V_{DD} = 5 \text{ V}$ 51020mVStep-up circuit	Input/output gain	A <sub>CS</sub>	$V_{\rm DD} = 5 \text{ V. } R_{\rm CS} = 0.33 \Omega$	0.36	0.48	0.60	A/V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Output	jie	all'e				
Torque limit current $I_{TL}$ $V_{DD} = 5$ V, $R_{CS} = 0.33$ Ω         455         570         685         mA           FG           FG output high-level         FG <sub>H</sub> $V_{DD} = 5$ V, $I_{FG} = -0.01$ mA         3         —         —         V           FG output low-level         FG <sub>L</sub> $V_{DD} = 5$ V, $I_{FG} = 0.01$ mA         —         —         0.5         V           In-phase input voltage range $V_{FGR}$ $V_{DD} = 5$ V         1.5         —         3.0         V           FG hysteresis width $H_{FG}$ $V_{DD} = 5$ V         5         10         20         mV           Step-up circuit	High-level output saturation voltage	Vо́н	$V_{DD} = 5 \text{ V}, I_{O} = -500 \text{ mA}$		0.15	0.30	V
Torque limit current $I_{TL}$ $V_{DD} = 5$ V, $R_{CS} = 0.33$ Ω         455         570         685         mA           FG           FG output high-level         FG <sub>H</sub> $V_{DD} = 5$ V, $I_{FG} = -0.01$ mA         3         —         —         V           FG output low-level         FG <sub>L</sub> $V_{DD} = 5$ V, $I_{FG} = 0.01$ mA         —         —         0.5         V           In-phase input voltage range $V_{FGR}$ $V_{DD} = 5$ V         1.5         —         3.0         V           FG hysteresis width $H_{FG}$ $V_{DD} = 5$ V         5         10         20         mV           Step-up circuit	Low-level output saturation voltage	VOL	$V_{DD} = 5 \text{ V}, I_{O} = 500 \text{ mA}$	_	0.15	0.30	V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Torque limit current	$I_{TL}$	$V_{DD} = 5 \text{ V}, R_{CS} = 0.33 \Omega$	455	570	685	mA
FG output low-level FG <sub>L</sub> $V_{DD} = 5 \text{ V}, I_{FG} = 0.01 \text{ mA}$ — 0.5 V  In-phase input voltage range $V_{FGR}$ $V_{DD} = 5 \text{ V}$ 1.5 — 3.0 V  FG hysteresis width $H_{FG}$ $V_{DD} = 5 \text{ V}$ 5 10 20 mV  Step-up circuit	FG						
In-phase input voltage range $V_{FGR}$ $V_{DD} = 5 \text{ V}$ $1.5 - 3.0 \text{ V}$ FG hysteresis width $H_{FG}$ $V_{DD} = 5 \text{ V}$ $5 \cdot 10 \cdot 20 \cdot \text{mV}$ Step-up circuit	FG output high-level	$FG_H$	$V_{DD} = 5 \text{ V}, I_{FG} = -0.01 \text{ mA}$	3	_	_	V
FG hysteresis width $H_{FG}$ $V_{DD} = 5 \text{ V}$ $5  10  20  \text{mV}$ Step-up circuit	FG output low-level	$FG_L$	$V_{DD} = 5 \text{ V}, I_{FG} = 0.01 \text{ mA}$	_	_	0.5	V
Step-up circuit	In-phase input voltage range	V <sub>FGR</sub>	$V_{DD} = 5 \text{ V}$	1.5	_	3.0	V
	FG hysteresis width	$H_{FG}$	$V_{DD} = 5 \text{ V}$	5	10	20	mV
Step-up voltage $V_{PUMP} V_{DD} = 5 V$ 7 — 10 V	Step-up circuit						
1000	Step-up voltage	V <sub>PUMP</sub>	$V_{DD} = 5 \text{ V}$	7	_	10	V

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# ■ Electrical Characteristics at T<sub>a</sub> = 25°C (continued)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
PWM oscillation changeover						
Input high-level	PWM <sub>H</sub>	$V_{DD} = 5 \text{ V}$	4.5	_	_	V
Input low-level	$PWM_L$	$V_{DD} = 5 \text{ V}$	_		0.5	V

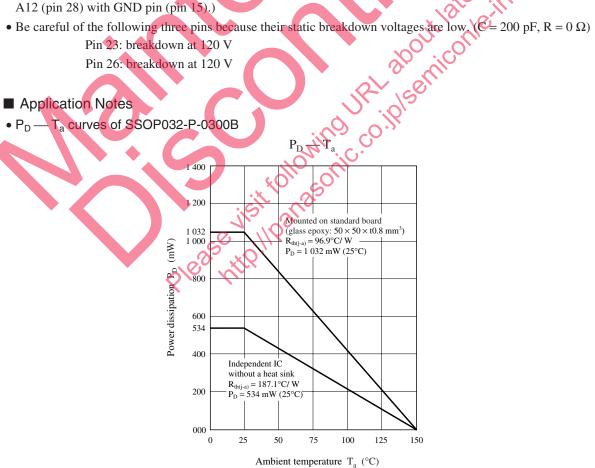
#### • Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max Unit
PWM oscillation changeover					
PWM frequency high-level	$f_{PWMH}$	$V_{DD} = 5 \text{ V}, \text{PWMSW} = \text{Low}$		80	— kHz
PWM frequency low-level	$f_{PWML}$	$V_{DD} = 5 \text{ V}, PWMSW = High}$		40	kHz
Thermal protection					
Thermal protection operating	T <sub>SDON</sub>	$V_{\rm DD} = 5 \text{ V}$		150	— °C
temperature			1 K		<b>%</b> .
Thermal protection hysteresis width	$\Delta T_{SD}$	$V_{DD} = 5 \text{ V}$	_	40	°C

## ■ Usage Notes

• Prevent this IC from being line-to-ground fault. (To be concrete, do not short-circuit any of A31 (pin 21), A32 (pin 22), A21 (pin 24), A22 (pin 25), A11 (pin 27) and A12 (pin 28) with GND pin (pin 15).)



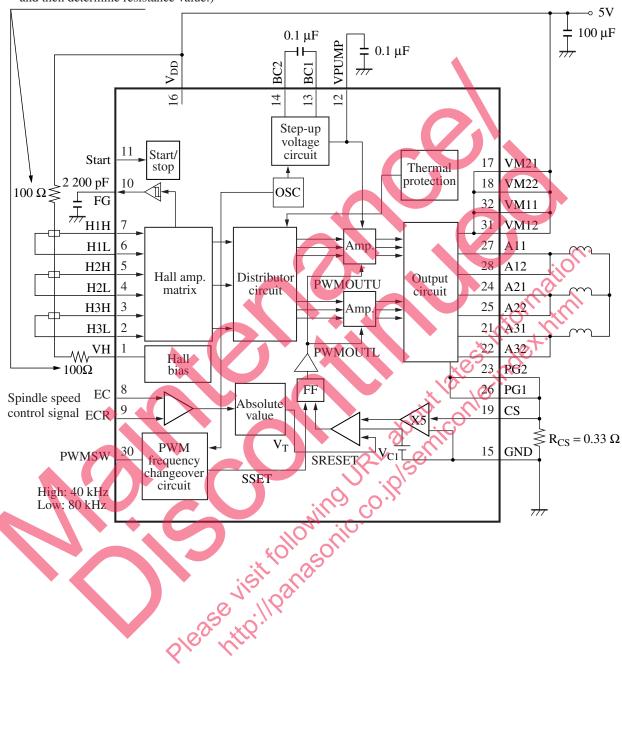
- Application Notes (continued)
- Phase conditions between Hall input and output current

Phase of Hall pin			n		
	H1H	H2H	H3H		
A	Н	ML	ML		
В	MH	L	MH		
C	ML	ML	Н		
D	L	MH	MH		
Е	ML	Н	ML		
F	MH	MH	L		
Er Output curre	mit A1	H1	H3	H2 H	H2 H3 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0
Output curre	nit		R 20	E F	

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### ■ Application Circuit Example

(Check the stipulated value of electrical characteristics and then determine resistance value.)



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